	Application No.	Applicant(s)	
Notice of Allowability			
	09/943,187 Examiner	CAMPBELL ET AL.	
	Khanh Duong	2822	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT F of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in i) or other appropriate comm RIGHTS. This application is to recommend the comment of the comment o	n this application. If not include unication will be mailed in due o	ed course. THIS
1. This communication is responsive to the amendment filed	on November 24, 2003.		
2. The allowed claim(s) is/are <u>1-51</u> .			
3. The drawings filed on 29 August 2001 are accepted by the			
 4. ☐ Acknowledgment is made of a claim for foreign priority u a) ☐ All b) ☐ Some* c) ☐ None of the: 	ınder 35 U.S.C. § 119(a)-(d)	or (f).	
 Certified copies of the priority documents hav 	e been received.		
Certified copies of the priority documents hav	e been received in Application	on No	
3. Copies of the certified copies of the priority do	ocuments have been receive	d in this national stage applicat	ion from the
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
5. Acknowledgment is made of a claim for domestic priority to reference was included in the first sentence of the specific			a specific
(a) 🔲 The translation of the foreign language provisional	application has been receive	d.	
6. Acknowledgment is made of a claim for domestic priority usin the first sentence of the specification or in an Application		or 121 since a specific referenc	e was included
Applicant has THREE MONTHS FROM THE "MAILING DATE" of below. Failure to timely comply will result in ABANDONMENT of			
7. A SUBSTITUTE OATH OR DECLARATION must be subminformal patent application (PTO-152) which give			OTICE OF
 8. ☐ CORRECTED DRAWINGS (as "replacement sheets") mu (a) ☐ including changes required by the Notice of Draftsper 1) ☐ hereto or 2) ☐ to Paper No 		w (PTO-948) attached	
(b) including changes required by the proposed drawing	correction filed whice	th has been approved by the Ex	kaminer.
(c) ☐ including changes required by the attached Examiner			
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in			back) of
9. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FOR			lote the
Attachment(s)			
1 ☐ Notice of References Cited (PTO-892)	5☐ Notice of Info	ormal Patent Application (PTO-	152)
 2 ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3 ☐ Information Disclosure Statements (PTO-1449 or PTO/SB Paper No 	6⊠ Interview Su	mmary (PTO-413), Paper No	·
	8), 7⊠ Examiner's A	Amendment/Comment	
4 Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's \$ 9∏ Other	Statement of Reasons for Allow	ance
		And the state of t	

Art Unit: 2822

DETAILED ACTION

Response to Amendment

This Office Action is in response to the amendment filed on November 24, 2003.

Accordingly, claim 34 was amended.

Currently, claims 1-51 are pending in the application.

Examiner's Amendment

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with James Darry on December 29, 2003.

The application has been amended as follows:

In the Claims:

Please amend claim 34 as follows:

line 11, after "said", delete "irradiated", and after "surface", insert --that has been irradiated--.

Allowable Subject Matter

Claims 1-51 are allowed.

The following is an examiner's statement of reasons for allowance: none of the prior art of record shows or fairly suggests all the process limitations as claimed. Specifically,

Art Unit: 2822

Re claim 1, none of the prior art of record discloses, in addition to other elements or processes as shown, the steps of: irradiating the silver effective to break a chalcogenide bond of the chalcogenide material at an interface of the silver comprising layer and chalcogenide material and diffuse at least some of the silver into the chalcogenide material, and forming an outer surface of the chalcogenide material; after the irradiating, exposing the chalcogenide material outer surface to an iodine comprising fluid effective to reduce roughness of the chalcogenide material outer surface from what it was prior to the exposing; and after exposing, depositing a second electrode material over the chalcogenide material, and forming the second conductive electrode material into an electrode of the device.

Re claim 11, none of the prior art of record discloses, in addition to other elements or processes as shown, the steps of after forming the chalcogenide comprising material, forming Ag_2Se over the chalcogenide comprising material; exposing the Ag_2Se to an iodine comprising fluid effective to etch away at least some of the Ag_2Se ; and after the exposing, depositing a second conductive electrode material over the chalcogenide material and forming the second conductive electrode material into an electrode of the device.

Re claim 20, none of the prior art of record discloses, in addition to other elements or processes as shown, the steps of: after forming the chalcogenide comprising material, forming a discontinuous layer of Ag_2Se over the chalcogenide comprising material; exposing the Ag_2Se to an iodine comprising fluid effective to etch away at least some of the Ag_2Se ; and after the exposing, depositing a second conductive electrode material over the chalcogenide material, and which is continuous and completely covering at least over the chalcogenide material, and forming the second conductive electrode material into an electrode of the device.

Art Unit: 2822

Re claim 26, none of the prior art of record discloses, in addition to other elements or processes as shown, the steps of irradiating the silver effective to break a chalcogenide bond of the chalcogenide material at an interface of the silver comprising layer and chalcogenide material and diffuse at least some of the silver into the chalcogenide material, the irradiating being effective to form a discontinuous layer of Ag₂Se over the chalcogenide comprising material, the irradiating being effective to maintain the chalcogenide material underlying the Ag₂Se in a substantially amorphous state; after the irradiating, exposing the Ag₂Se to an iodine comprising fluid effective to etch away at least a majority of the Ag₂Se; and after exposing, depositing a second electrode material over the chalcogenide material, and which is continuous and completely covering at least over the chalcogenide material, and forming the second conductive electrode material into an electrode of the device.

Re claim 34, none of the prior art of record discloses, in addition to other elements or processes as shown, the steps of: *irradiating the metal-containing layer to break a chalcogenide bond of the chalcogenide glass layer at the interface of the metal-containing layer and chalcogenide glass layer, such that at least a portion of the metal-containing layer diffuses into the chalcogenide glass layer; and after the step of irradiating, exposing an outer surface of the chalcogenide glass layer to an iodine comprising fluid, wherein the iodine comprising fluid removes at least a portion of the outer surface that has been irradiated.*

Re claim 42, none of the prior art of record discloses, in addition to other elements or processes as shown, the steps of: irradiating the metal-containing layer to break a chalcogenide bond of the chalcogenide glass layer at the interface of the metal-containing layer and chalcogenide glass layer thereby creating an outside surface; removing at least a portion of the

Art Unit: 2822

outside surface by etching with an iodine comprising fluid; and, after the step of removing at least a portion of the outside surface, forming a second conductive layer over at least a portion of the outside surface remaining after the act of removing.

Re claim 51, none of the prior art of record discloses, in addition to other elements or processes as shown, the steps of: irradiating the metal-containing layer to break a chalcogenide bond of the chalcogenide glass layer at the interface of the metal-containing layer and chalcogenide glass layer thereby creating an outside surface; the step of irradiating is effective to form Ag_2Se as at least part of the outside surface; removing at least a portion of the outside surface by etching with an iodine comprising fluid, said etching being effective to etch away at least some of the Ag_2Se ; and, after the step of removing at least a portion of the outside surface, forming a second conductive layer over at least a portion of the outside surface remaining after the act of removing.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khanh Duong whose telephone number is (571) 272-1836. The examiner can normally be reached on Monday - Friday (9:00 AM - 6:00 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian, can be reached on (571) 272-1852. The fax phone numbers for the

Art Unit: 2822

organization where this application or proceeding is assigned are (703) 305-3431 for regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

KBD

December 29, 2003

ATERIZARANAM

THE STATE OF THE S